

AOZ8851ADI

Ultra Low Capacitance One-line
Bidirectional TVS Diode

General Description

The AOZ8851ADI is an ultra low capacitance one-line bidirectional transient voltage suppressor diode designed to protect high speed data lines and voltage sensitive electronics from high transient conditions and ESD.

This device incorporates one bidirectional TVS diode in an ultra-small 0201 footprint package. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15 kV air, ±15 kV contact discharge).

The AOZ8851ADI comes in an RoHS compliant package and is rated over a -40 °C to +85 °C ambient temperature range.

The ultra-small 0.62 mm x 0.32 mm x 0.3 mm 0201 footprint package makes the AOZ8851ADI ideal for applications where PCB space is a premium. The small size and high ESD protection makes it ideal for protecting voltage sensitive electronics from high transient conditions and ESD.

Features

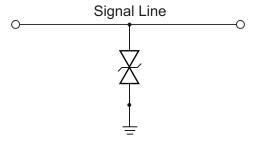
- ESD protection for high-speed data lines:
 - Exceeds: IEC 61000-4-2 (ESD) ±20 kV (air), ±20 kV (contact)
 - Human Body Model (HBM) ±25 kV
- Small package saves board space
- Ultra low capacitance: 0.22 pF
- Low clamping voltage
- Low operating voltage: 3.3 V, 5 V
- Pb-free device

Applications

- Portable handheld devices
- Keypads, data lines, buttons
- Notebook computers
- Digital Cameras
- Portable GPS



Typical Application



Bidirection Protection of Single Line

Pin Configuration





Ordering Information

Part Number	Ambient Temperature Range	Package	Environmental		
AOZ8851ADI-03	-40 °C to +85 °C	DFN 0.62 x 0.32	Green Product		
AOZ8851ADI-05	-40 C to +65 C	DFN 0.02 X 0.32	RoHS Compliant		



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant. Please visit www.aosmd.com/media/AOSGreenPolicy.pdf for additional information.

Absolute Maximum Ratings

Exceeding the Absolute Maximum Ratings may damage the device.

Parameter	Rating			
VP – VN	3.3 V	5 V		
Peak Pulse Current (I_{PP}), t_P = 8/20 μ s	4 A	4 A		
Storage Temperature (T _S)	-65 °C to +150 °C	-65 °C to +150 °C		
ESD Rating per IEC61000-4-2, Contact ⁽¹⁾	±20 kV	±20 kV		
ESD Rating per IEC61000-4-2, Air ⁽¹⁾	±20 kV	±20 kV		
ESD Rating per Human Body Model ⁽²⁾	±15 kV	±15 kV		

Notes:

- 1. IEC 61000-4-2 discharge with C_Discharge = 150 pF, R_Discharge = 330 Ω .
- 2. Human Body Discharge per MIL-STD-883, Method 3015 $C_{Discharge}$ = 100 pF, $R_{Discharge}$ = 1.5 k Ω .

Maximum Operating Conditions

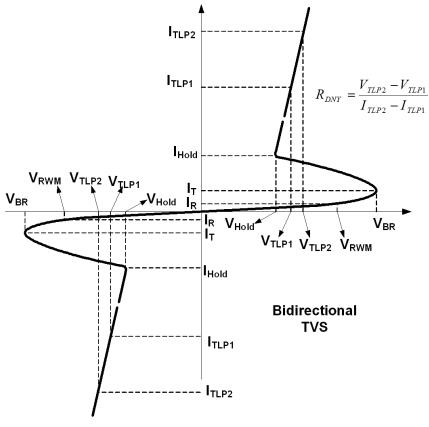
The device is not guaranteed to operate beyond the Maximum Operating Conditions.

Parameter	Rating
Junction Temperature (T _J)	-40 °C to +125 °C



Electrical Characteristics

T_A = 25°C unless otherwise specified.



AOZ8851	AOZ8851ADI-03										
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units					
V _{RWM}	Reverse Working Voltage	I/O Pin to ground			3.3	V					
V _{BR}	Reverse Breakdown Voltage	I _T =1mA, I/O Pin to ground	4.6			V					
I _R	Reverse Leakage Current	V _{RWM} =3.3V, I/O Pin to ground			100	nA					
V _{CL}	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} =16A I _{TLP} =-16A		16 -16	20 -20	V					
	I/O Pin to ground)	I _{TLP} =30A I _{TLP} =-30A		23 -23	28 -28	V					
	Clamping Voltage ⁽³⁾ (IEC61000-4-5, 8/20µs, I/O Pin to ground)	I _{PP} =4A I _{PP} =-4A		11 -11	13 -13	V					
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 10A to 30A I _{TLP} = -10A to -30A		0.5 0.5		Ω					
CJ	Junction Capacitance	V _{I/O} =0V, f=1MHz, I/O Pin to ground		0.22	0.35	pF					
		V _{I/O} =0V, f=1GHz, I/O Pin to ground		0.19	0.29	pF					

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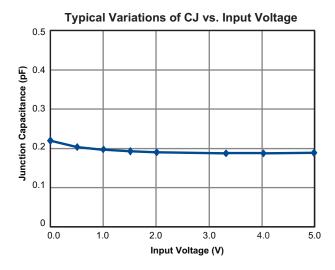
AOZ8851ADI-05										
Symbol Parameter		Conditions	Min.	Min. Typ.		Units				
V _{RWM}	Reverse Working Voltage	I/O Pin to ground			5	V				
V _{BR}	Reverse Breakdown Voltage	I _T =1mA, I/O Pin to ground	6.5			V				
I _R	Reverse Leakage Current	V _{RWM} =5V, I/O Pin to ground			100	nA				
V _{CL}	Clamping Voltage ⁽³⁾ (100ns Transmission Line Pulse,	I _{TLP} =16A I _{TLP} =-16A		17 -17	20 -20	V				
	I/O Pin to ground)	I _{TLP} =30A I _{TLP} =-30A	25 -25	28 -28	V					
	Clamping Voltage ⁽³⁾ (IEC61000-4-5, 8/20µs, I/O Pin to ground)	I _{PP} =4A I _{PP} =-4A		11.5 -11.5	13 -13	V				
R _{DNY}	Dynamic Resistance ⁽³⁾	I _{TLP} = 10A to 30A I _{TLP} = -10A to -30A		0.5 0.5		Ω				
CJ	Junction Capacitance	V _{I/O} =0V, f=1MHz, I/O Pin to ground		0.22	0.35	pF				
		V _{I/O} =0V, f=1GHz, I/O Pin to ground		0.19	0.29	pF				

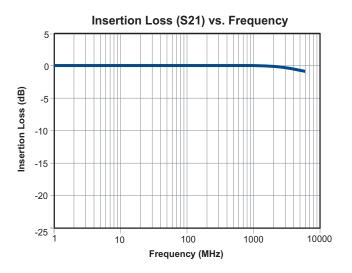
Note:

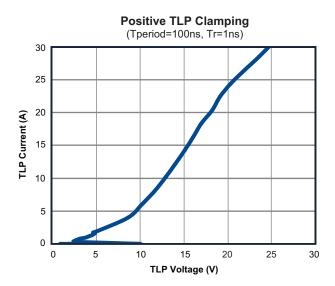
^{3.} These specifications are guaranteed by design and characterization.

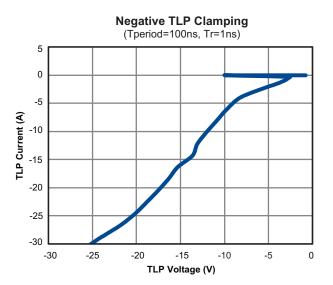


Typical Performance Characteristics



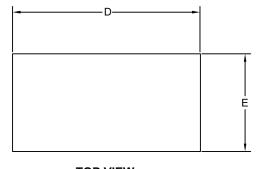








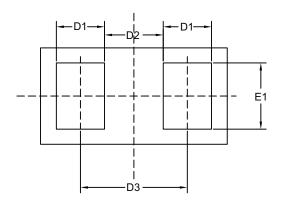
Package Dimensions, DFN 0.62x0.32, 2L EP2 S





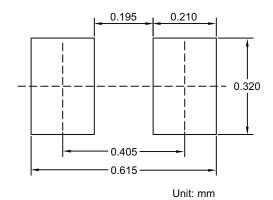


SIDE VIEW



BOTTTOM VIEW

RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
Α	0.27	0.30	0.33
D	0.57 0.62 0		0.67
D1	0.11	0.16	0.21
D2	0.145	0.195	0.245
D3	0.305	0.355	0.405
E	0.27	0.32	0.37
E1	0.17	0.22	0.27
E1	0.17	0.22	0.2

Dimensions in inches

Symbols	Min.	Nom.	Max.
Α	0.0106	0.0118	0.0130
D	0.0224	0.0244	0.0264
D1	0.0043	0.0063	0.0083
D2	0.0057	0.0077	0.0097
D3	0.0120	0.0140	0.0167
E	0.0106	0.0126	0.0146
E1	0.0067	0.0087	0.0107

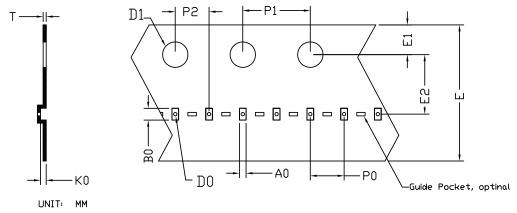
Notes:

- 1. All dimensions are in millimeters.
- 2. Dimensions are inclusive of plating.
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6mil each.
- 4. Controlling dimension is millimeter. Converted inch dimensions are not necessarily exact.
- 5. Paddle exposed on bottom.



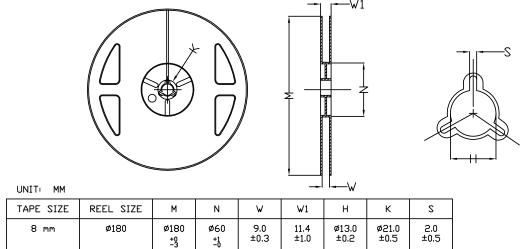
Tape and Reel Dimensions, DFN 0.62x0.32

Carrier Tape



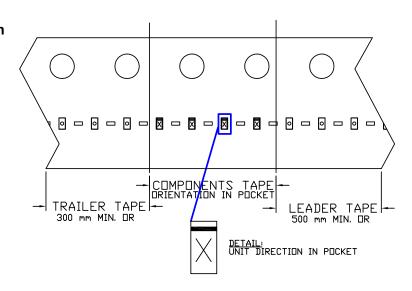
PACKAGE	A0	В0	K0	D0	D1	Ε	E1	E2	P0	P1	P2	Т
DFN0.62×0.32 (8 mm)	0.39 ±0.03	0.69 ±0.03	0.34 +0.03 -0.01	0.20 ±0.05	1.50 +0.1 -0.0	8.00 ±0.10	1.75 ±0.10	3.50 ±0.03	2.00 ±0.05	4.00 ±0.05	2.00 ±0.05	0.20 ±0.05

Reel



Leader / Trailer & Orientation

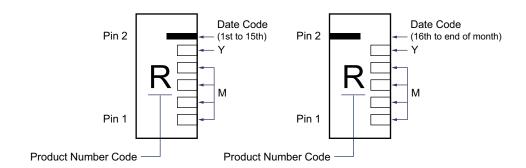
Unit Per Reel: 10000pcs



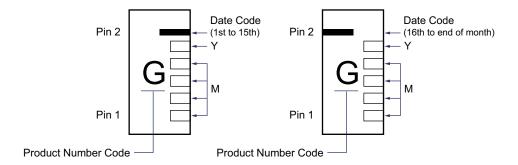


Part Marking

AOZ8851ADI-03 (DFN0.62x0.32)



AOZ8851ADI-05 (DFN0.62x0.32)



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- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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